

Brightened emission of dark trions in transition metal dichalcogenide monolayers

V. Jindal¹

K. Mourzidis¹, A. Balocchi¹, C. Robert¹, P. Li², D. Van Tuan², L. Lombez¹, D. Lagarde¹, P. Renucci¹, T. Taniguchi³, K. Watanabe⁴, H. Dery^{2,5} and X. Marie^{1,6}

¹Université de Toulouse, INSA-CNRS-UPS, LPCNO, 135 Av. Rangueil, 31077 Toulouse, France

² Department of Electrical and Computer Engineering, University of Rochester, Rochester, New York 14627, USA

³International Center for Materials Nanoarchitectonics, National Institute for Materials Science, 1-1 Namiki, Tsukuba 305-00044, Japan⁴

⁴Research Center for Functional Materials, National Institute for Materials Science, 1-1 Namiki, Tsukuba 305-00044, Japan

⁵Department of Physics and Astronomy, University of Rochester, Rochester, New York 14627, USA

⁶Institut Universitaire de France, 75231 Paris, France

jjindal@insa-toulouse.fr

The optical properties of atomically thin semiconductors based on transition-metal dichalcogenides (TMDs) are dominated by robust exciton complexes, such as the fascinating recombination processes of bright and dark trions [1]. The use of charge-tunable TMD monolayers fully encapsulated in hexagonal boron nitride (hBN) allows us to electrostatically dope the monolayers and significantly enhance the resolution of these complexes. Moderate electron doping of WSe₂ monolayers leads to the emergence of a strong luminescence peak just below the well-understood spectral lines associated with the recombination of negatively charged bright and dark trions. This peak has been observed by multiple research groups [2]. Two fundamental questions emerge: which exciton complex is associated with this optical recombination? What is the mechanism by which the recombination process works? In this work, polarization-dependent micro-photoluminescence (PL) experiments are performed at 4 K to demonstrate that this luminescence peak is the result of electron-electron assisted recombination that brightens the dark trion emission. Supporting evidence for this second-order recombination process comes from identifying the equivalent brightened emission of positively charged dark trions when the monolayer is electrostatically doped with holes. Remarkably, the discovered hole-hole-assisted PL peak emerges in the near infrared, about 500 meV below the well-studied spectral region of excitons and trions. Further, with magneto-PL experiments, we find that the g-factor of this new transition ($g = +4$) has an opposite sign compared to the well-known g-factor of neutral or charged excitons. This allows us to propose a brightening mechanism for the positively charged dark trion involving the Γ valence band [3].

References

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